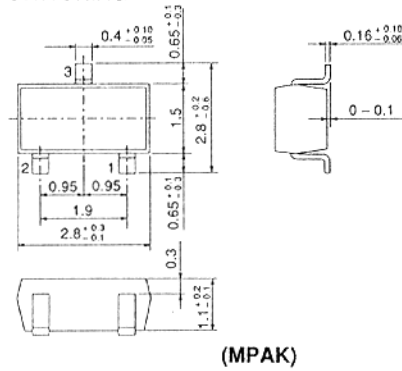


2SA1666

SILICON PNP EPITAXIAL

HIGH FREQUENCY AMPLIFIER-SWITCHING

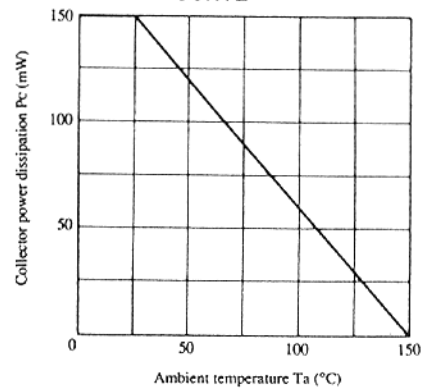


1. Emitter
 2. Base
 3. Collector
- (Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1666	Unit
Collector to base voltage	V _{CB0}	-20	V
Collector to emitter voltage	V _{CE0}	-15	V
Emitter to base voltage	V _{EB0}	-4	V
Collector current	I _C	-200	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{sig}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-20	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, R _{BE} = ∞	-15	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C = 0	-4	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -16V, I _E = 0	—	—	-0.2	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -2V, I _C = 0	—	—	-0.2	μA
DC current transfer ratio	h _{FE}	V _{CE} = -0.5V, I _C = -30mA	20	—	200	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -30mA, I _B = -1mA	—	—	-0.5	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = -30mA, I _B = -1mA	—	—	-1.0	V
Turn on time	t _{on}	I _C = -30mA, I _{B1} = -I _{B2} = -3mA	—	35	—	ns
Turn off time	t _{off}	I _C = -30mA, I _{B1} = -I _{B2} = -3mA	—	70	—	ns

* Marking is "Y1-".

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